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BTS7008-2EPA

PROFET™+2 12V

2x 8 mΩ

Smart High-Side Power Switch



Package	PG-TSDSO-14-22
Marking	7008-2A

1 Overview

Application

- Suitable for resistive, inductive and capacitive loads
- Replaces electromechanical relays, fuses and discrete circuits
- Driving capability suitable for 7.5 A loads and high inrush current loads such as H9 65W / Xenon 65W lamps or LED equivalent

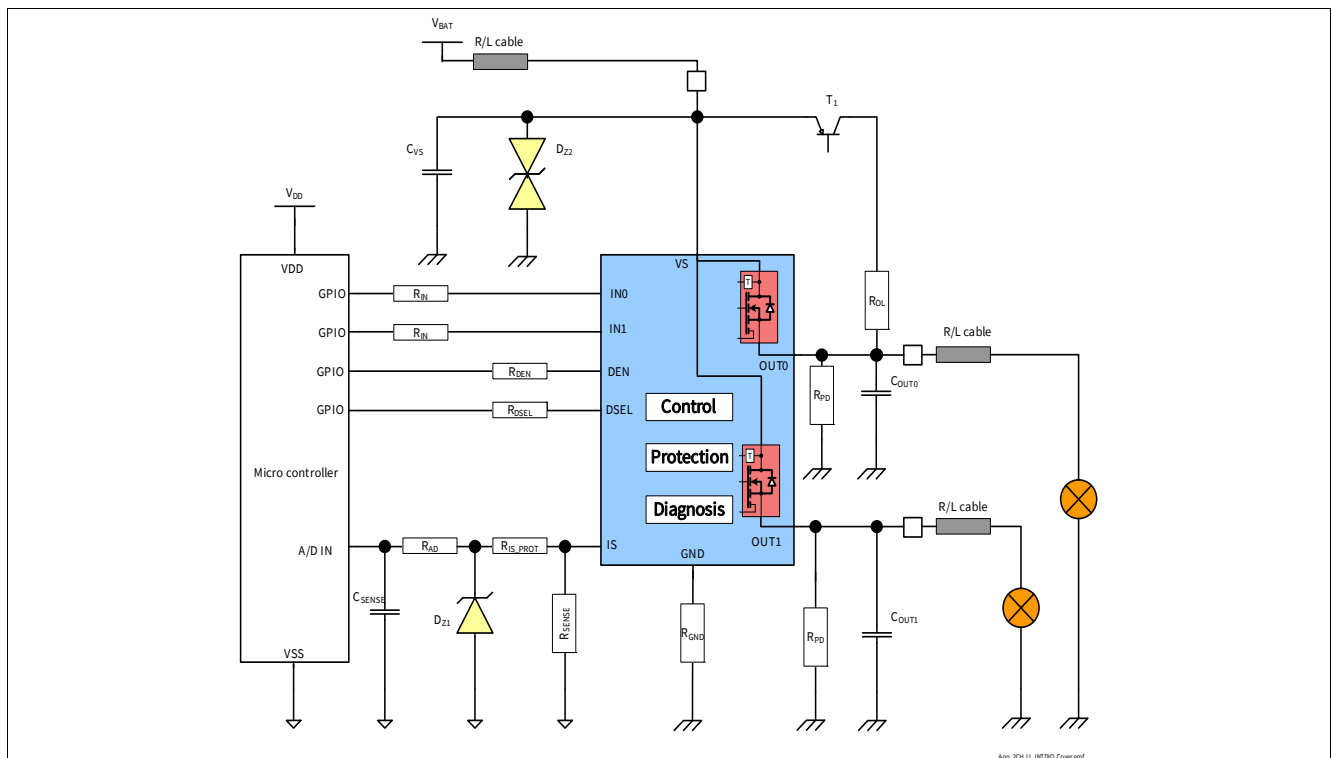
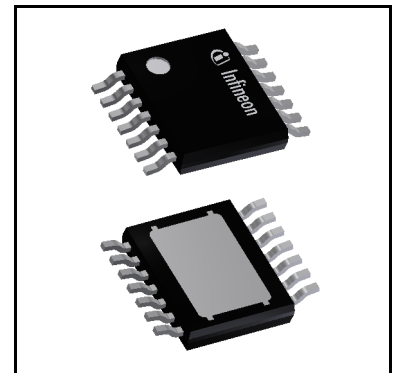


Figure 1 BTS7008-2EPA Application Diagram. Further information in [Chapter 10](#)

Overview

Basic Features

- High Side Switch with Diagnosis and Embedded Protection
- Part of PROFET™+2 12V Family
- ReverSave™ for low power dissipation in Reverse Polarity
- Green Product (RoHS compliant)
- Qualified in accordance with AEC Q100 grade 1

Protection Features

- Absolute and dynamic temperature limitation with controlled restart
- Over Current protection (tripping) with Intelligent Restart Control
- Under Voltage shutdown
- Over Voltage Protection with external components

Diagnostic Features

- Proportional load current sense
- Open Load in ON and OFF state
- Short circuit to ground and battery

Description

The BTS7008-2EPA is a Smart High-Side Power Switch 8 mΩ Dual channel, providing protection functions and diagnosis. The device is integrated in SMART7 technology.

Table 1 Product Summary

Parameter	Symbol	Values
Minimum Operating voltage (at switch ON)	$V_{S(OP)}$	4.1 V
Minimum Operating voltage (cranking)	$V_{S(UV)}$	3.1 V
Maximum Operating voltage	V_S	28 V
Minimum overvoltage protection @ 25 °C	$V_{DS(CLAMP)}$	35 V
Maximum current in Sleep mode ($T_J \leq 85$ °C)	$I_{VS(SLEEP)}$	0.6 μA
Maximum operative current	$I_{GND(ACTIVE)}$	5 mA
Maximum ON-state resistance ($T_J = 150$ °C)	$R_{DS(ON)}$	16 mΩ
Nominal load current ($T_A = 85$ °C)	$I_{L(NOM)}$	7.5 A
Typical current sense ratio at $I_L = I_{L(NOM)}$	k_{ILIS}	5500

Block Diagram and Terms

2 Block Diagram and Terms

2.1 Block Diagram

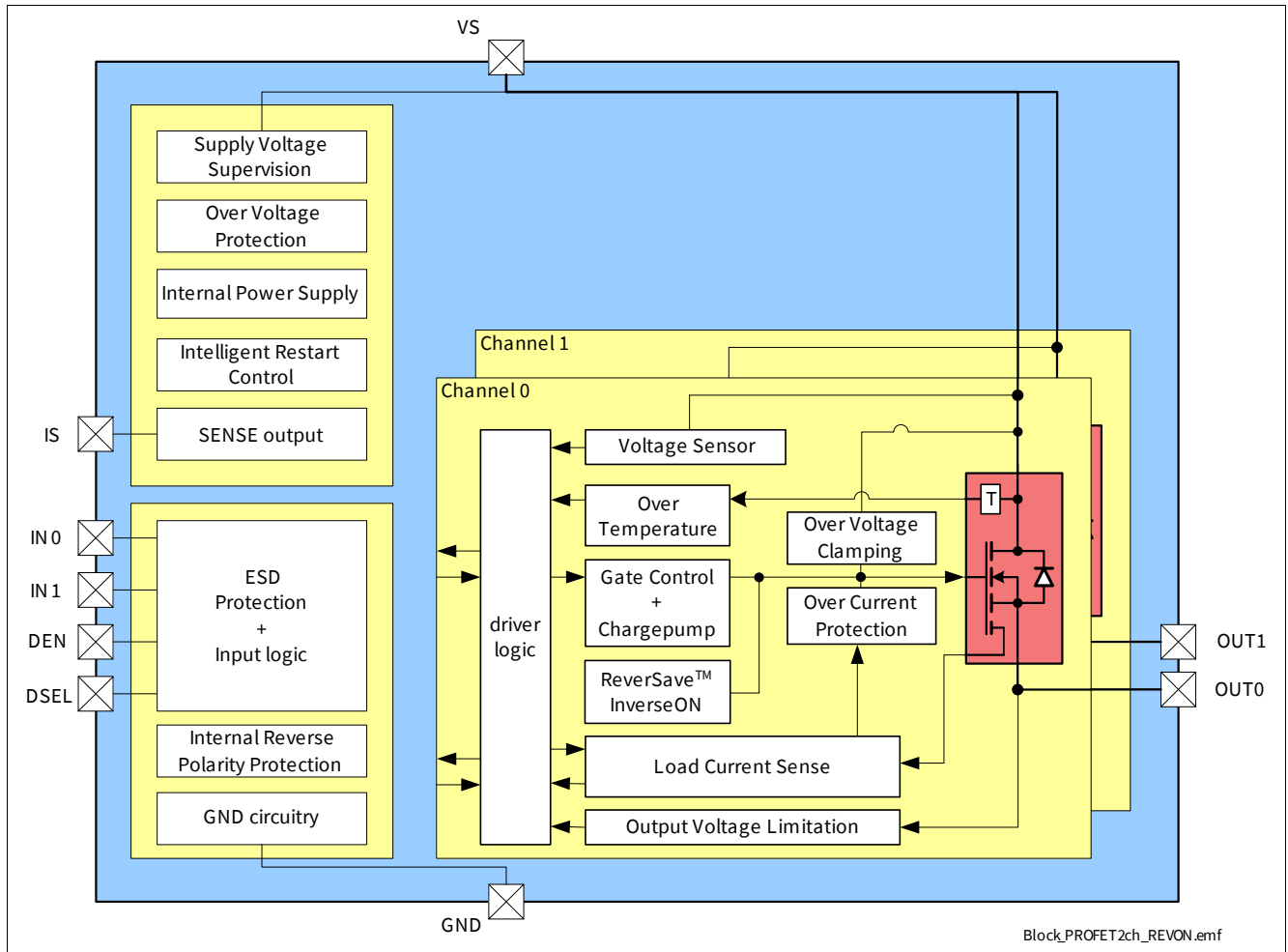


Figure 2 Block Diagram of BTS7008-2EPA

Block Diagram and Terms

2.2 Terms

Figure 3 shows all terms used in this data sheet, with associated convention for positive values.

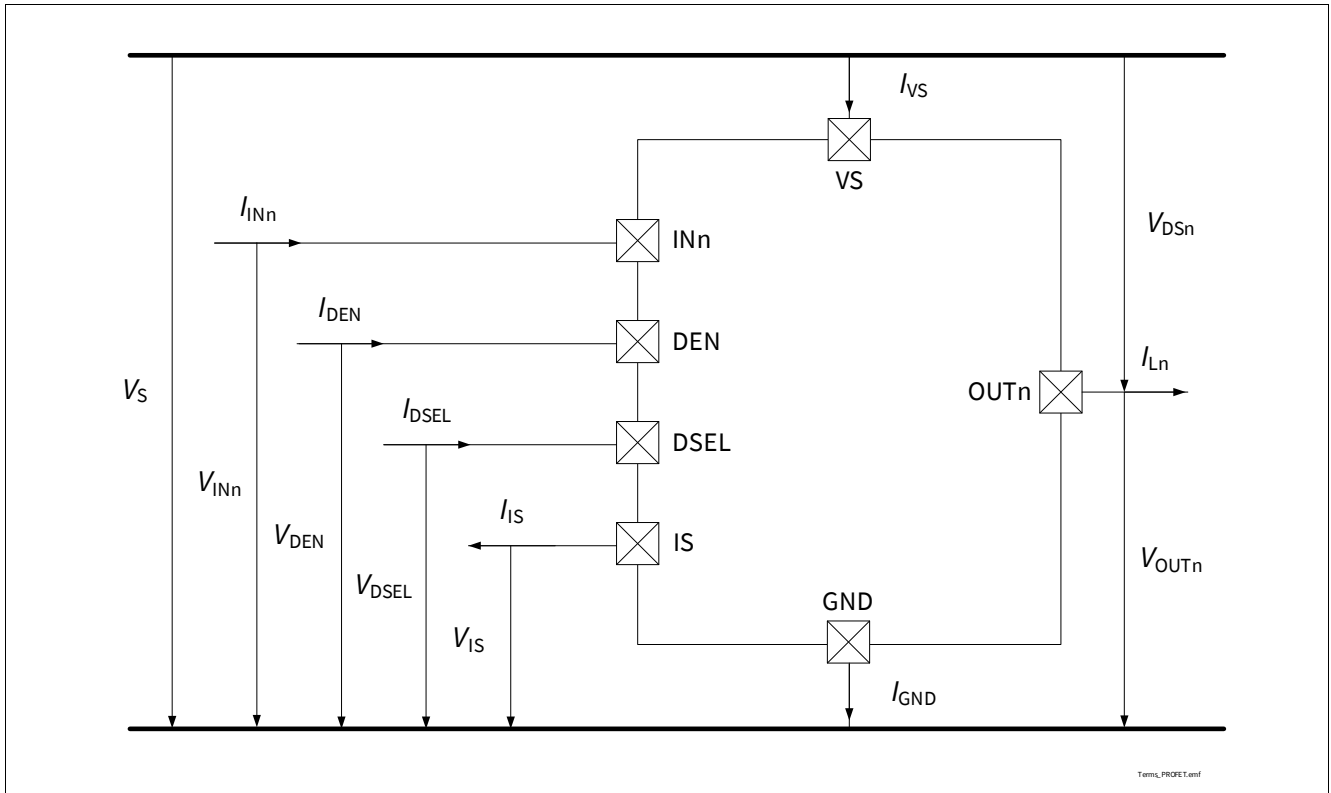


Figure 3 Voltage and Current Convention

Pin Configuration

3 Pin Configuration

3.1 Pin Assignment

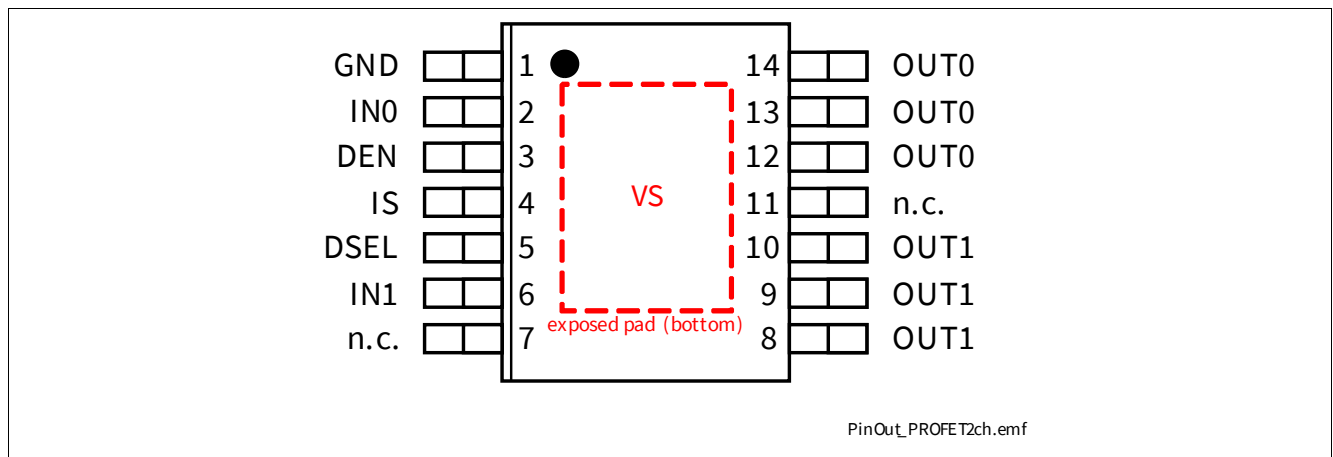


Figure 4 Pin Configuration

Pin Configuration

3.2 Pin Definitions and Functions

Table 2 Pin Definition

Pin	Symbol	Function
EP	VS (exposed pad)	Supply Voltage Battery voltage
1	GND	Ground Signal ground
2, 6	INn	Input Channel n Digital signal to switch ON channel n (“high” active) If not used: connect to GND pin or to module ground with a 10 kΩ resistor
3	DEN	Diagnostic Enable Digital signal to enable device diagnosis (“high” active) and to clear the protection counter of channel selected with DSEL pin If not used: connect to GND pin or to module ground with a 10 kΩ resistor
4	IS	SENSE current output Analog/digital signal for diagnosis If not used: left open
5	DSEL	Diagnosis Selection Digital signal to select one channel to perform ON and OFF state diagnosis (“high” active) If not used: connect to GND pin or to module ground with a 10 kΩ resistor
7, 11	n.c.	Not connected, internally not bonded
8-10, 12-14	OUTn	Output n Protected high-side power output channel n ¹⁾

1) All output pins of the channel must be connected together on the PCB. All pins of the output are internally connected together. PCB traces have to be designed to withstand the maximum current which can flow

General Product Characteristics

4 General Product Characteristics

4.1 Absolute Maximum Ratings - General

Table 3 Absolute Maximum Ratings¹⁾

$T_J = -40\text{ °C}$ to $+150\text{ °C}$; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Supply pins							
Power Supply Voltage	V_S	-0.3	–	28	V	–	P_4.1.0.1
Load Dump Voltage	$V_{BAT(LD)}$	–	–	35	V	suppressed Load Dump acc. to ISO16750-2 (2010). $R_f = 2\ \Omega$	P_4.1.0.3
Supply Voltage for Short Circuit Protection	$V_{BAT(SC)}$	0	–	24	V	Setup acc. to AEC-Q100-012	P_4.1.0.25
Reverse Polarity Voltage	$-V_{BAT(REV)}$	–	–	16	V	$t \leq 2\text{ min}$ $T_A = +25\text{ °C}$ Setup as described in Chapter 10	P_4.1.0.5
Current through GND Pin	I_{GND}	-50	–	50	mA	R_{GND} according to Chapter 10	P_4.1.0.9

Logic & control pins (Digital Input = DI)

DI = INn, DEN, DSEL

Current through DI Pin	I_{DI}	-1	–	2	mA	²⁾	P_4.1.0.14
Current through DI Pin Reverse Battery condition	I_{DI}	-1	–	10	mA	²⁾ $t \leq 2\text{ min}$	P_4.1.0.36

IS pin

Voltage at IS Pin	V_{IS}	-1.5	–	V_S	V	$I_{IS} = 10\ \mu\text{A}$	P_4.1.0.16
Current through IS Pin	I_{IS}	-25	–	$I_{IS(SAT),M}$ AX	mA	–	P_4.1.0.18

Temperatures

Junction Temperature	T_J	-40	–	150	°C	–	P_4.1.0.19
Storage Temperature	T_{STG}	-55	–	150	°C	–	P_4.1.0.20

ESD Susceptibility

General Product Characteristics

Table 3 Absolute Maximum Ratings¹⁾ (continued)

$T_J = -40\text{ °C}$ to $+150\text{ °C}$; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
ESD Susceptibility all Pins (HBM)	$V_{ESD(HBM)}$	-2	-	2	kV	HBM ³⁾	P_4.1.0.21
ESD Susceptibility OUTn vs GND and VS connected (HBM)	$V_{ESD(HBM)_{OU T}}$	-4	-	4	kV	HBM ³⁾	P_4.1.0.22
ESD Susceptibility all Pins (CDM)	$V_{ESD(CDM)}$	-500	-	500	V	CDM ⁴⁾	P_4.1.0.23
ESD Susceptibility Corner Pins (CDM) (pins 1, 7, 8, 14)	$V_{ESD(CDM)_{CR N}}$	-750	-	750	V	CDM ⁴⁾	P_4.1.0.24

- 1) Not subject to production test - specified by design.
- 2) Maximum V_{DI} to be considered for Latch-Up tests: 5.5 V
- 3) ESD susceptibility, HBM according to ANSI/ESDA/JEDEC JS001 (1.5 kΩ, 100 pF)
- 4) ESD susceptibility, Charged Device Model “CDM” according JEDEC JESD22-C101

Notes

1. Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
2. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as “outside” normal operating range. Protection functions are not designed for continuous repetitive operation.

4.2 Absolute Maximum Ratings - Power Stages

4.2.1 Power Stage - 8 mΩ

Table 4 Absolute Maximum Ratings¹⁾

$T_J = -40\text{ °C}$ to $+150\text{ °C}$; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Maximum Energy Dissipation Single Pulse	E_{AS}	-	-	75	mJ	$I_L = 2 \cdot I_{L(NOM)}$ $T_{J(0)} = 150\text{ °C}$ $V_S = 28\text{ V}$	P_4.2.1.1

General Product Characteristics

Table 4 Absolute Maximum Ratings¹⁾ (continued)

$T_J = -40\text{ °C}$ to $+150\text{ °C}$; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Maximum Energy Dissipation Repetitive Pulse	E_{AR}	–	–	25	mJ	$I_L = I_{L(NOM)}$ $T_{J(0)} = 85\text{ °C}$ $V_S = 13.5\text{ V}$ 1M cycles	P_4.2.1.2
Load Current	$ I_L $	–	–	$I_{L(OVL),M}$ AX	A		P_4.2.1.3

1) Not subject to production test - specified by design.

4.3 Functional Range

Table 5 Functional Range - Supply Voltage and Temperature¹⁾

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Supply Voltage Range for Normal Operation	$V_{S(NOR)}$	6	13.5	18	V	–	P_4.3.0.1
Lower Extended Supply Voltage Range for Operation	$V_{S(EXT,LOW)}$	3.1	–	6	V	²⁾³⁾ (parameter deviations possible)	P_4.3.0.2
Upper Extended Supply Voltage Range for Operation	$V_{S(EXT,UP)}$	18	–	28	V	²⁾ (parameter deviations possible)	P_4.3.0.3
Junction Temperature	T_J	-40	–	150	°C	–	P_4.3.0.5

1) Not subject to production test - specified by design.

2) Protection functions still operative

3) In case of V_S voltage decreasing: $V_{S(EXT,LOW),MIN} = 3.1\text{ V}$. In case of V_S voltage increasing: $V_{S(EXT,LOW),MIN} = 4.1\text{ V}$

Note: *Within the functional or operating range, the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the Electrical Characteristics table.*

General Product Characteristics

4.4 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to www.jedec.org.

Table 6 Thermal Resistance¹⁾

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Thermal Resistance Junction to Case	R_{thJC}	–	3	5	K/W	²⁾	P_4.4.0.1
Thermal Resistance Junction to Soldering Point	R_{thJSP}	–	3	5	K/W	²⁾ simulated at exposed pad	P_4.4.0.2
Thermal Resistance Junction to Ambient	R_{thJA}	–	33	–	K/W	²⁾	P_4.4.0.3

- 1) Not subject to production test - specified by design.
- 2) Specified R_{thJA} value is according to Jeduc JESD51-2,-5,-7 at natural convection on FR4 2s2p board; The Product (Chip + Package) was simulated on a 76.2 × 114.3 × 1.5 mm board with 2 inner copper layers (2 × 70 μm Cu, 2 × 35 μm Cu). Where applicable a thermal via array under the exposed pad contacted the first inner copper layer. Simulation done at $T_{AMB} = 105^{\circ}C$.

4.4.1 PCB set up

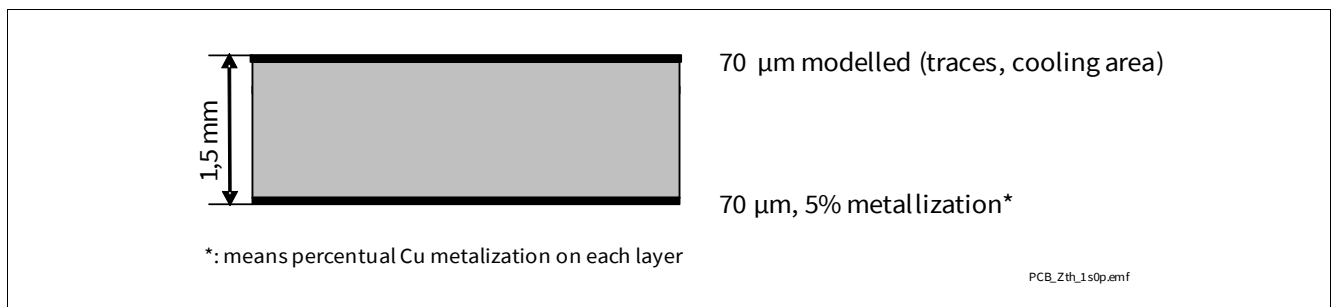


Figure 5 1s0p PCB Cross Section

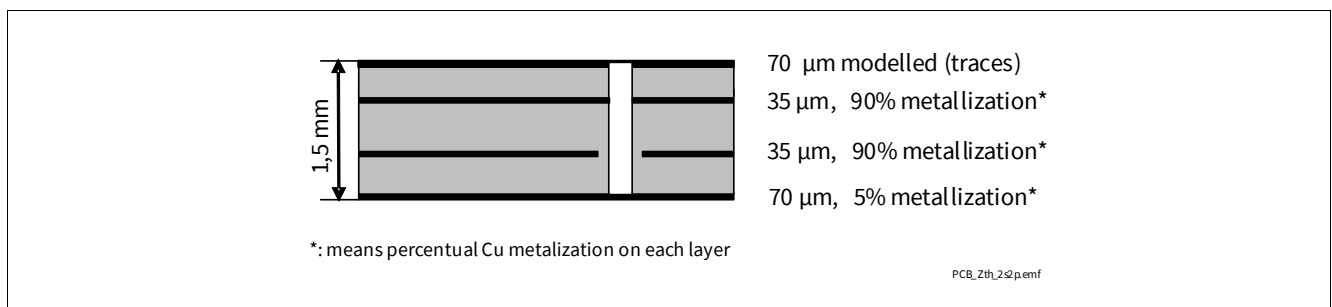


Figure 6 2s2p PCB Cross Section

General Product Characteristics

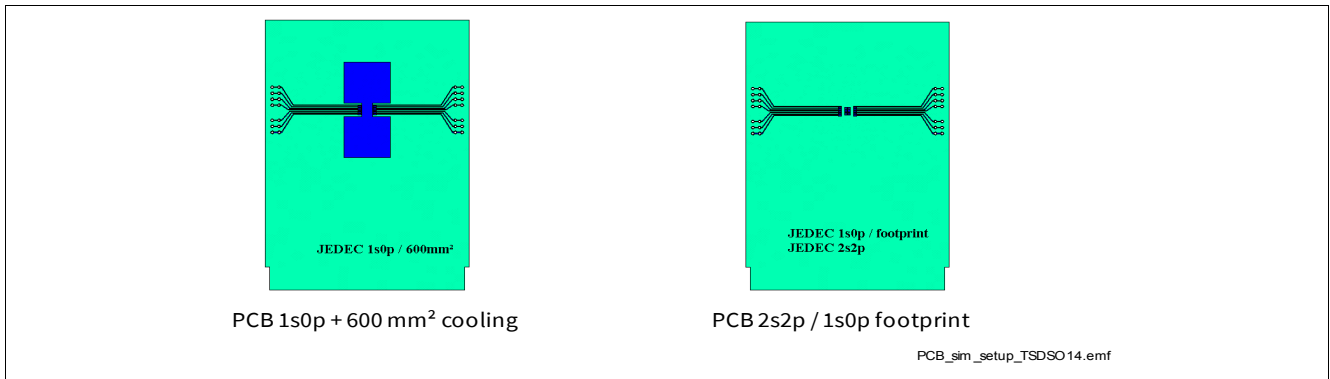


Figure 7 PCB setup for thermal simulations

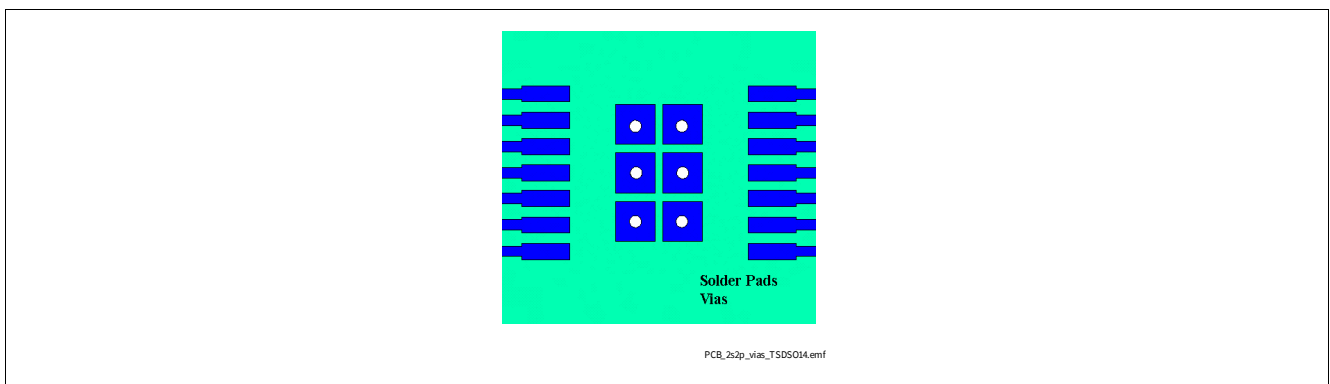


Figure 8 Thermal vias on PCB for 2s2p PCB setup

4.4.2 Thermal Impedance

General Product Characteristics

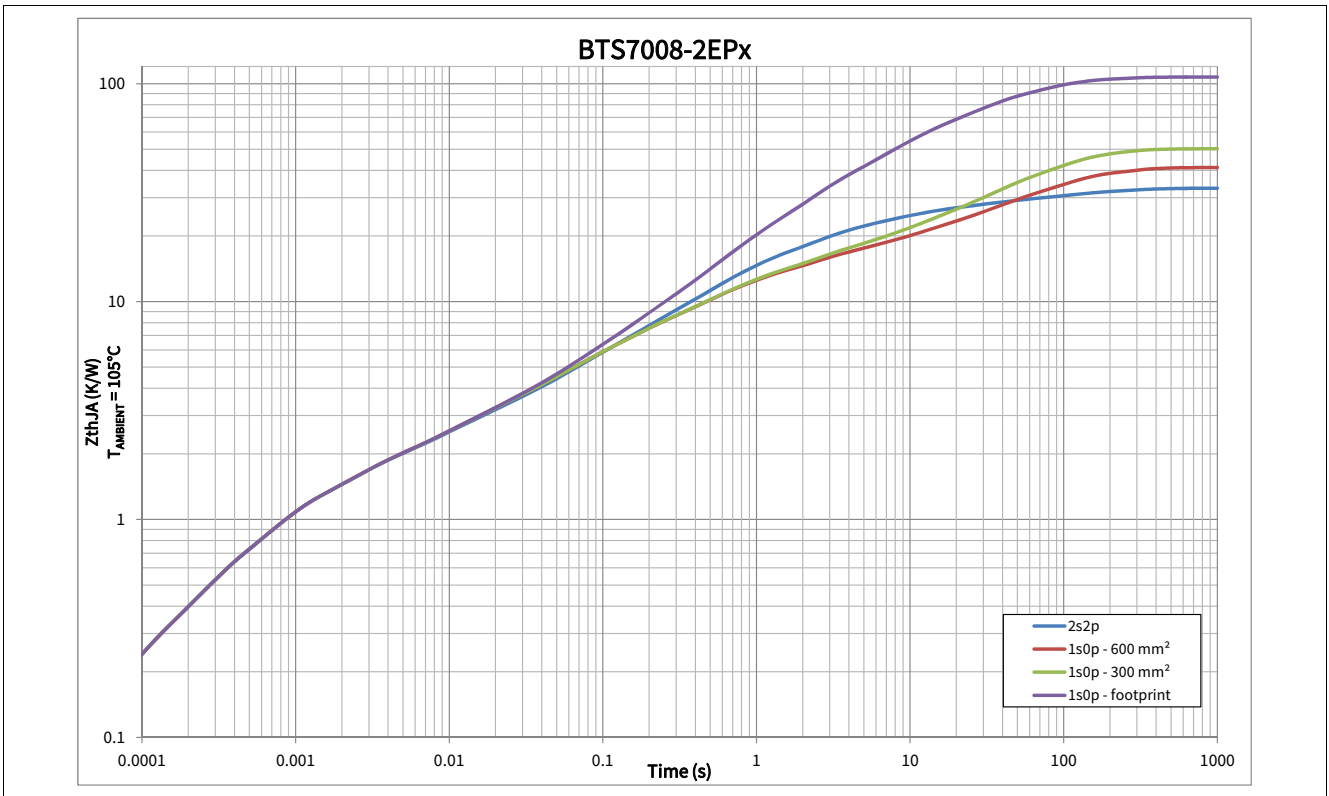


Figure 9 Typical Thermal Impedance. PCB setup according [Chapter 4.4.1](#)

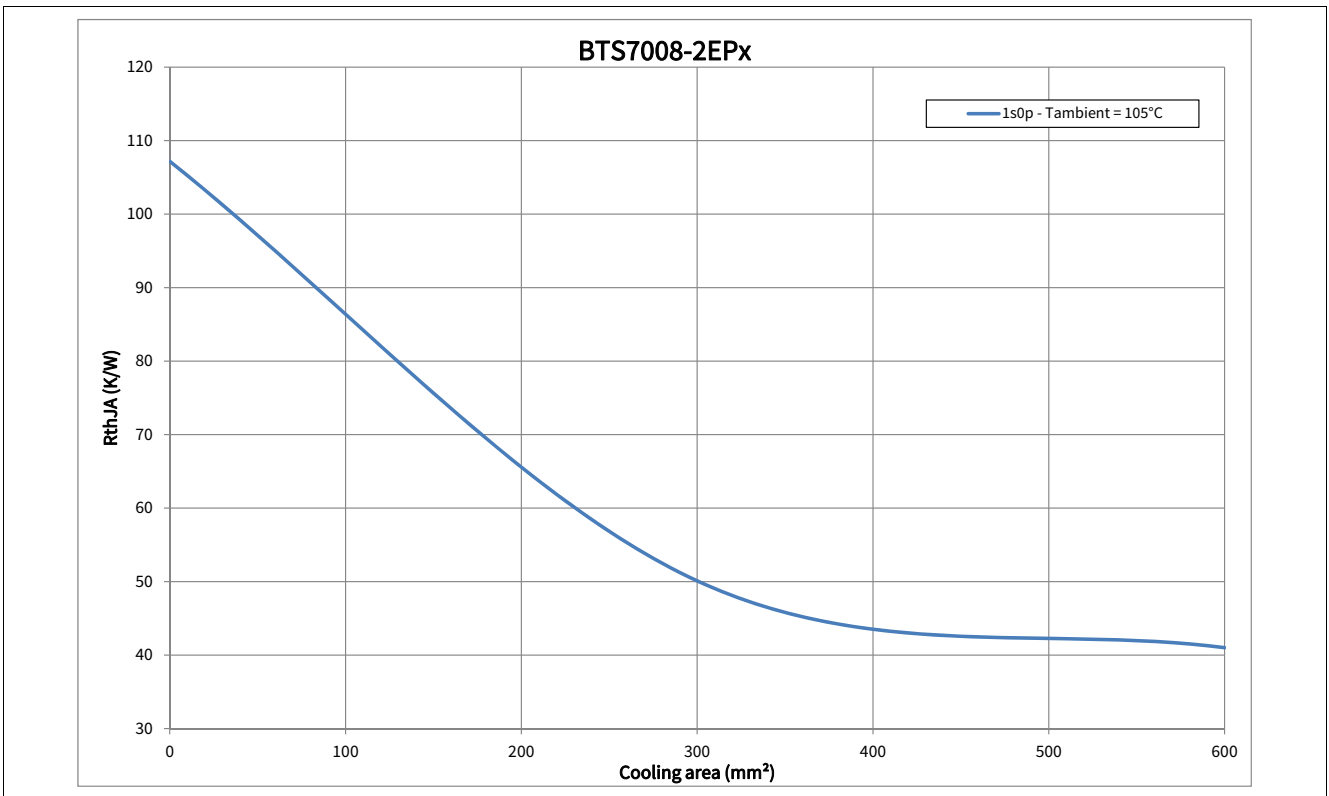


Figure 10 Thermal Resistance on 1s0p PCB with various cooling surfaces

Logic Pins

5 Logic Pins

The device has 4 digital pins for direct control.

5.1 Input Pins (INn)

The input pins IN0, IN1 activate the corresponding output channel. The input circuitry is compatible with 3.3V and 5V micro-controller. The electrical equivalent of the input circuitry is shown in **Figure 11**. In case the pin is not used, it must be connected to module ground or to device GND pin with a 10 kΩ resistor.

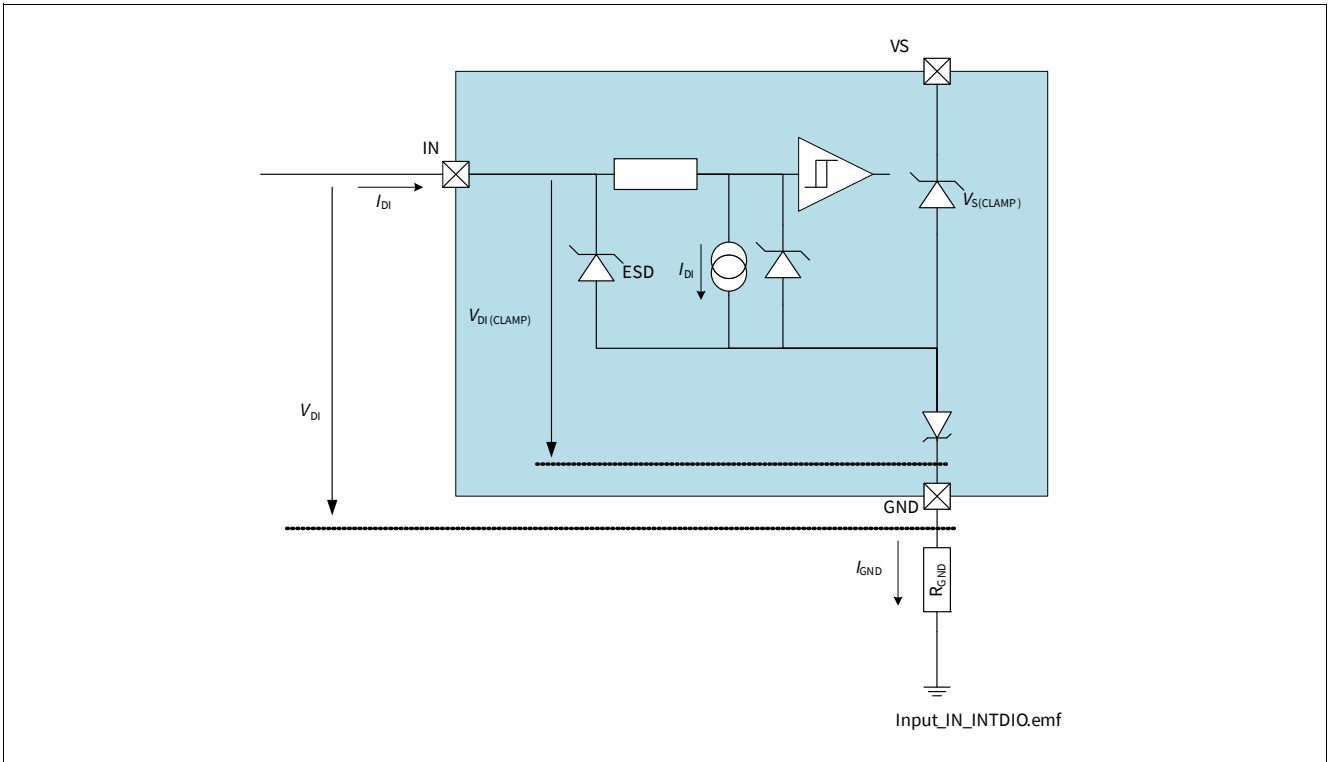


Figure 11 Input circuitry

The logic thresholds for “low” and “high” states are defined by parameters $V_{DI(TH)}$ and $V_{DI(HYS)}$. The relationship between these two values is shown in **Figure 12**. The voltage V_{IN} needed to ensure an “high” state is always higher than the voltage needed to ensure a “low” state.

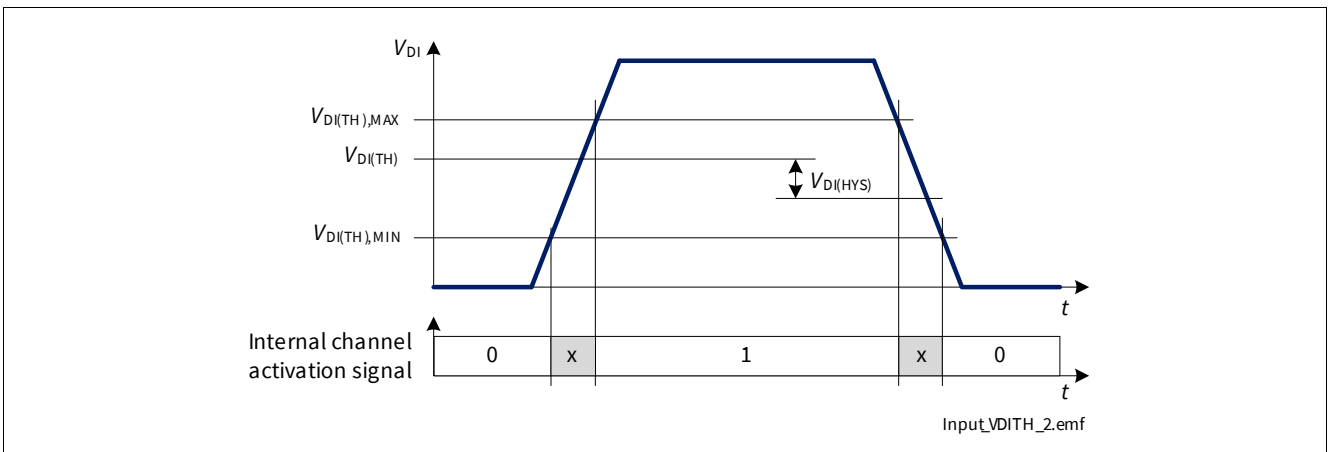


Figure 12 Input Threshold voltages and hysteresis

5.2 Diagnosis Pin

The Diagnosis Enable (DEN) pin controls the diagnosis circuitry and the protection circuitry. When DEN pin is set to “high”, the diagnosis is enabled (see [Chapter 9.2](#) for more details). When it is set to “low”, the diagnosis is disabled (IS pin is set to high impedance).

The Diagnosis Selection (DSEL) pin selects the channel where diagnosis is performed (see [Chapter 9.1.1](#)).

The transition from “high” to “low” of DEN pin clears the protection latch of the channel selected with DSEL pin depending on the logic state of IN pin and DEN pulse length (see [Chapter 8.3](#) for more details). The internal structure of diagnosis pins is the same as the one of input pins. See [Figure 11](#) for more details.

Logic Pins

5.3 Electrical Characteristics Logic Pins

$V_S = 6\text{ V to }18\text{ V}$, $T_J = -40\text{ °C to }+150\text{ °C}$

Typical values: $V_S = 13.5\text{ V}$, $T_J = 25\text{ °C}$

Digital Input (DI) pins = IN, DEN, DSEL

Table 7 Electrical Characteristics: Logic Pins - General

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Digital Input Voltage Threshold	$V_{DI(TH)}$	0.8	1.3	2	V	See Figure 11 and Figure 12	P_5.4.0.1
Digital Input Clamping Voltage	$V_{DI(CLAMP1)}$	–	7	–	V	¹⁾ $I_{DI} = 1\text{ mA}$ See Figure 11 and Figure 12	P_5.4.0.2
Digital Input Clamping Voltage	$V_{DI(CLAMP2)}$	6.5	7.5	8.5	V	$I_{DI} = 2\text{ mA}$ See Figure 11 and Figure 12	P_5.4.0.3
Digital Input Hysteresis	$V_{DI(HYS)}$	–	0.25	–	V	¹⁾ See Figure 11 and Figure 12	P_5.4.0.4
Digital Input Current (“high”)	I_{DI}	2	10	25	μA	$V_{DI} = 2\text{ V}$ See Figure 11 and Figure 12	P_5.4.0.5
Digital Input Current (“low”)	I_{DI}	2	10	25	μA	$V_{DI} = 0.8\text{ V}$ See Figure 11 and Figure 12	P_5.4.0.6

1) Not subject to production test - specified by design

6 Power Supply

The BTS7008-2EPA is supplied by V_S , which is used for the internal logic as well as supply for the power output stages. V_S has an undervoltage detection circuit, which prevents the activation of the power output stages and diagnosis in case the applied voltage is below the undervoltage threshold.

6.1 Operation Modes

BTS7008-2EPA has the following operation modes:

- Sleep mode
- Active mode
- Stand-by mode

The transition between operation modes is determined according to these variables:

- logic level at INn pins
- logic level at DEN pin

The state diagram including the possible transitions is shown in [Figure 13](#). The behavior of BTS7008-2EPA as well as some parameters may change in dependence from the operation mode of the device. Furthermore, due to the undervoltage detection circuitry which monitors V_S supply voltage, some changes within the same operation mode can be seen accordingly.

There are three parameters describing each operation mode of BTS7008-2EPA:

- status of the output channel
- status of the diagnosis
- current consumption at VS pin (measured by I_{VS} in Sleep mode, I_{GND} in all other operative modes)

[Table 8](#) shows the correlation between operation modes, V_S supply voltage, and the state of the most important functions (channel status, diagnosis).

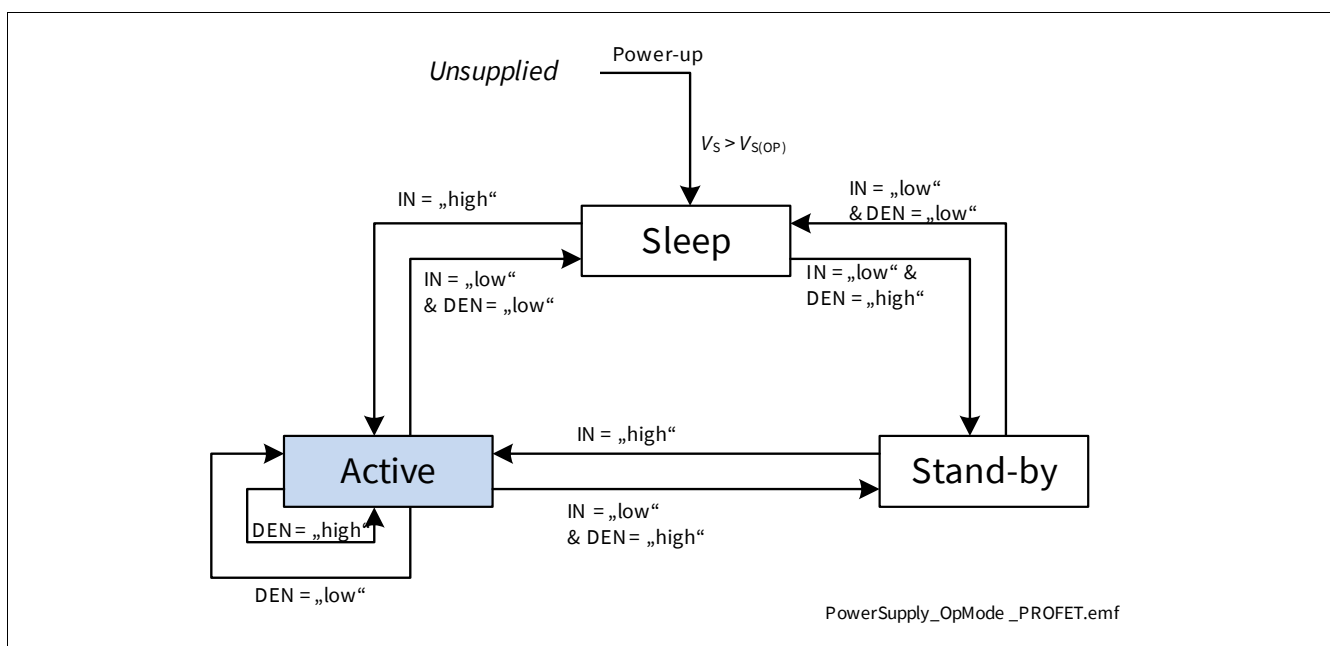


Figure 13 Operation Mode State Diagram

Power Supply

Table 8 Device function in relation to operation modes and V_S voltage

Operative Mode	Function	V_S in undervoltage	V_S not in undervoltage
Sleep	Channel	OFF	OFF
	Diagnosis	OFF	OFF
Active	Channels	OFF	available
	Diagnosis	OFF	available in OFF and ON states
Stand-by	Channels	OFF	OFF
	Diagnosis	OFF	available in OFF state

6.1.1 Unsupplied

In this state, the device is either unsupplied (no voltage applied to VS pin) or the supply voltage is below the undervoltage threshold.

6.1.2 Power-up

The Power-up condition is entered when the supply voltage (V_S) is applied to the device. The supply is rising until it is above the undervoltage threshold $V_{S(OP)}$ therefore the internal power-on signals are set.

6.1.3 Sleep mode

The device is in Sleep mode when all Digital Input pins (INn, DEN, DSEL) are set to “low”. When BTS7008-2EPA is in Sleep mode, all outputs are OFF. The current consumption is minimum (see parameter $I_{VS(SLEEP)}$). No Over Temperature or Overload protection mechanism is active when the device is in Sleep mode. The device can go in Sleep mode only if the protection is not active (counter = 0, see [Chapter 8.3.1](#) for further details).

6.1.4 Stand-by mode

The device is in Stand-by mode as long as DEN pin is set to “high” while input pins are set to “low”. All channels are OFF therefore only Open Load in OFF diagnosis is possible. Depending on the load condition, either a fault current $I_{IS(Fault)}$ or an Open Load in OFF current $I_{IS(OLOFF)}$ may be present at IS pin. In such situation, the current consumption of the device is increased.

6.1.5 Active mode

Active mode is the normal operation mode of BTS7008-2EPA. The device enters Active mode as soon as one IN pin is set to “high”. Device current consumption is specified with $I_{GND(Active)}$ (measured at GND pin because the current at VS pin includes the load current). Overload, Over Temperature and Over Voltage protections are active. Diagnosis is available.

6.2 Undervoltage on V_S

Between $V_{S(OP)}$ and $V_{S(UV)}$ the undervoltage mechanism is triggered. If the device is operative (in Active mode) and the supply voltage drops below the undervoltage threshold $V_{S(UV)}$, the internal logic switches OFF the output channels.

As soon as the supply voltage V_S is above the operative threshold $V_{S(OP)}$, the channels having the corresponding input pin set to “high” are switched ON again. The restart is delayed with a time $t_{DELAY(UV)}$ which protects the device in case the undervoltage condition is caused by a short circuit event (according to AEC-Q100-012), as shown in [Figure 14](#).

Power Supply

If the device is in Sleep mode and one input is set to “high”, the corresponding channel is switched ON if $V_S > V_{S(OP)}$ without waiting for $t_{DELAY(UV)}$.

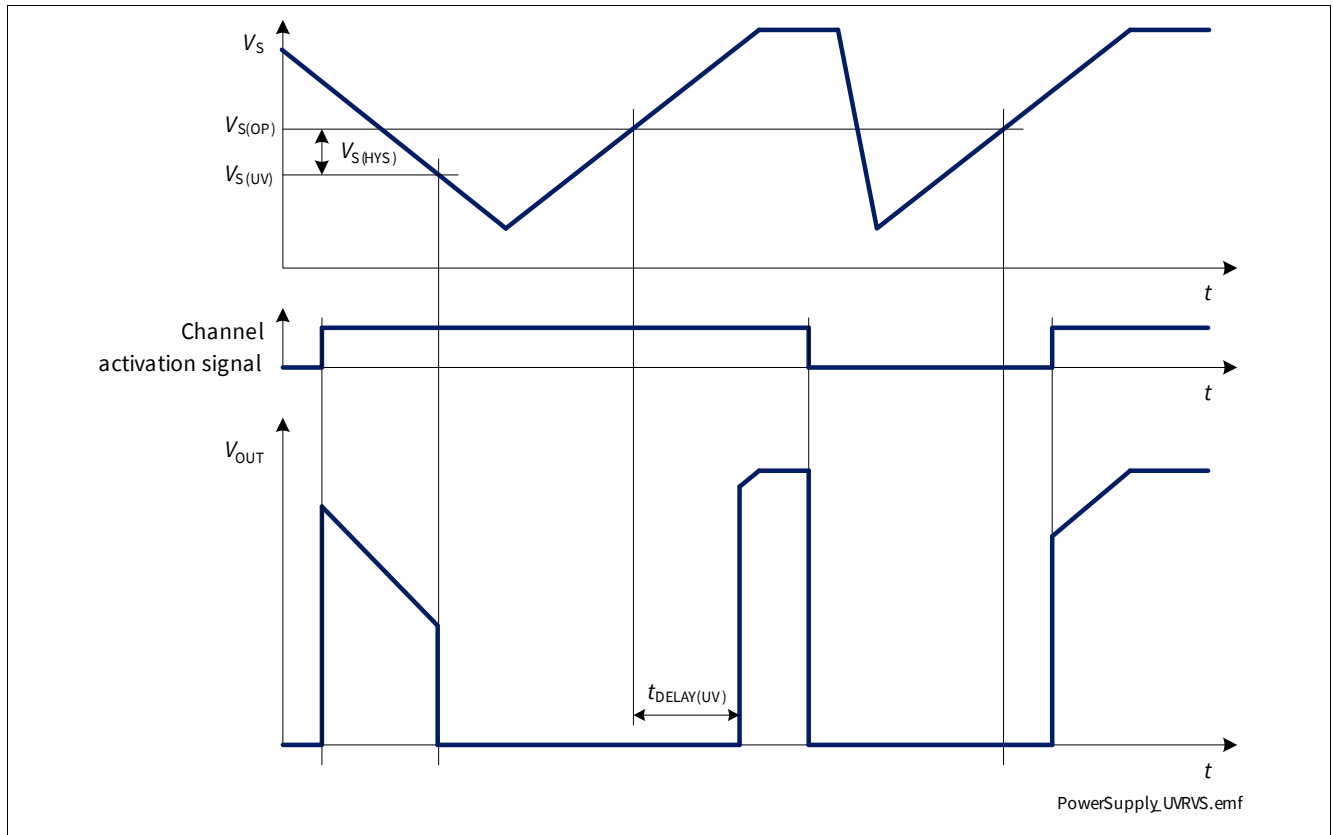


Figure 14 V_S undervoltage behavior

Power Supply

6.3 Electrical Characteristics Power Supply

$V_S = 6\text{ V to }18\text{ V}$, $T_J = -40\text{ °C to }+150\text{ °C}$

Typical values: $V_S = 13.5\text{ V}$, $T_J = 25\text{ °C}$

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

$R_L = 3.3\ \Omega$

Table 9 Electrical Characteristics: Power Supply - General

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
VS pin							
Power Supply Undervoltage Shutdown	$V_{S(UV)}$	1.8	2.3	3.1	V	V_S decreasing IN = "high" From $V_{DS} \leq 0.5\text{ V}$ to $V_{DS} = V_S$ See Figure 14	P_6.4.0.1
Power Supply Minimum Operating Voltage	$V_{S(OP)}$	2.0	3.0	4.1	V	V_S increasing IN = "high" From $V_{DS} = V_S$ to $V_{DS} \leq 0.5\text{ V}$ See Figure 14	P_6.4.0.3
Power Supply Undervoltage Shutdown Hysteresis	$V_{S(HYS)}$	–	0.7	–	V	¹⁾ $V_{S(OP)} - V_{S(UV)}$ See Figure 14	P_6.4.0.6
Power Supply Undervoltage Recovery Time	$t_{DELAY(UV)}$	2.5	5	7.5	ms	$dV_S/dt \leq 0.5\text{ V}/\mu\text{s}$ $V_S \geq -1\text{ V}$ See Figure 14	P_6.4.0.7
Breakdown Voltage between GND and VS Pins in Reverse Battery	$-V_{S(REV)}$	16	–	30	V	¹⁾ $I_{GND(REV)} = 7\text{ mA}$ $T_J = 150\text{ °C}$	P_6.4.0.9

1) Not subject to production test - specified by design

6.4 Electrical Characteristics Power Supply - product specific

6.4.1 BTS7008-2EPA

Power Supply

Table 10 Electrical Characteristics: Power Supply BTS7008-2EPA

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Power Supply Current Consumption in Sleep Mode with Loads at $T_J \leq 85\text{ °C}$	$I_{VS(SLEEP)_85}$	–	0.03	0.6	μA	1) $V_S = 18\text{ V}$ $V_{OUT} = 0\text{ V}$ IN = DEN = “low” $T_J \leq 85\text{ °C}$ see Figure 3	P_6.5.1.1
Power Supply Current Consumption in Sleep Mode with Loads at $T_J = 150\text{ °C}$	$I_{VS(SLEEP)_150}$	–	5	20	μA	$V_S = 18\text{ V}$ $V_{OUT} = 0\text{ V}$ IN = DEN = “low” $T_J = 150\text{ °C}$ see Figure 3	P_6.5.1.2
Operating Current in Active Mode (all Channels ON)	$I_{GND(ACTIVE)}$	–	3	4	mA	$V_S = 18\text{ V}$ IN = DEN = “high” see Figure 3	P_6.5.1.3
Operating Current in Stand-by Mode	$I_{GND(STBY)}$	–	1.2	1.8	mA	$V_S = 18\text{ V}$ IN = “low” DEN = “high” see Figure 3	P_6.5.1.5

1) Not subject to production test - specified by design

Power Stages

7 Power Stages

The high-side power stages are built using a N-channel vertical Power MOSFET with charge pump.

7.1 Output ON-State Resistance

The ON-state resistance $R_{DS(ON)}$ depends mainly on junction temperature T_J . **Figure 15** shows the variation of $R_{DS(ON)}$ across the whole T_J range. The value “2” on the y-axis corresponds to the maximum $R_{DS(ON)}$ measured at $T_J = 150\text{ °C}$.

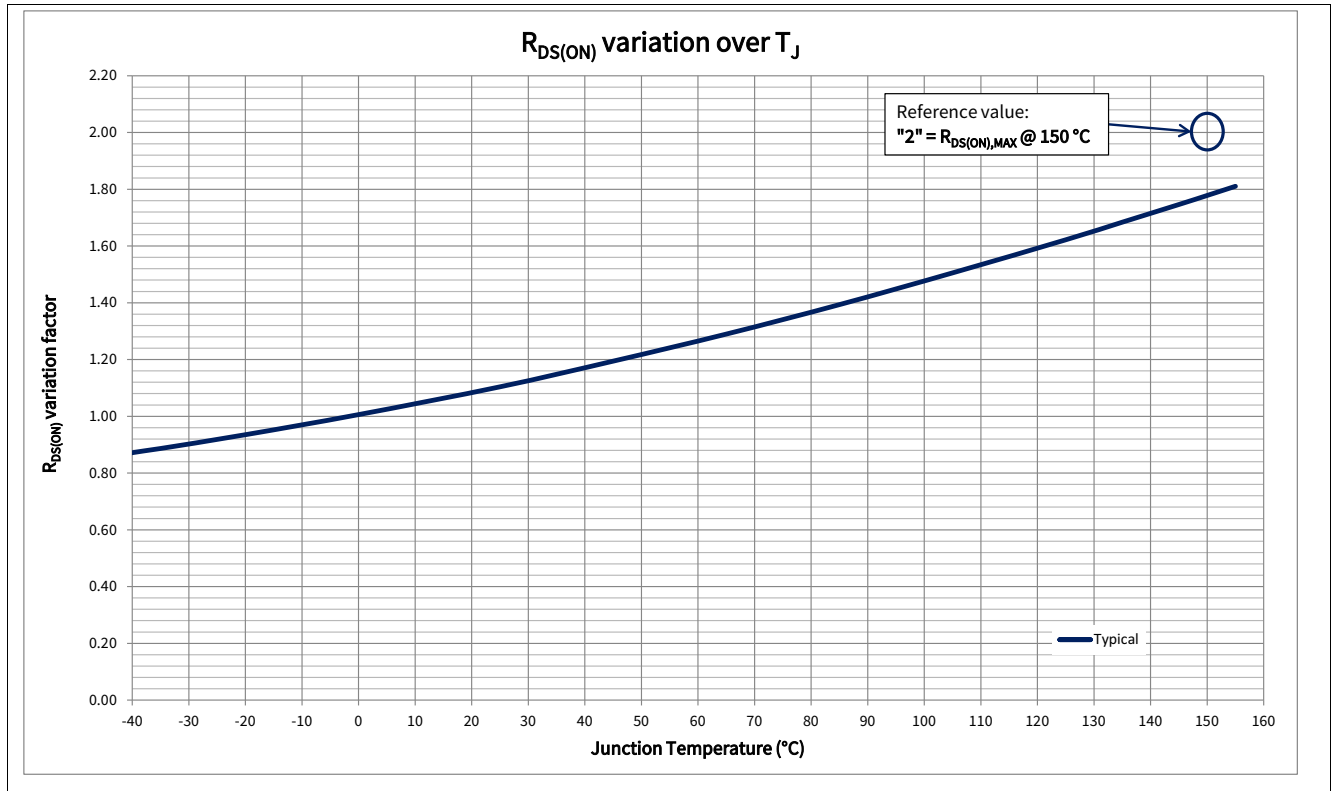


Figure 15 $R_{DS(ON)}$ variation factor

The behavior in Reverse Polarity is described in [Chapter 8.4.1](#).

7.2 Switching loads

7.2.1 Switching Resistive Loads

When switching resistive loads, the switching times and slew rates shown in **Figure 16** can be considered. The switch energy values E_{ON} and E_{OFF} are proportional to load resistance and times t_{ON} and t_{OFF} .

Power Stages

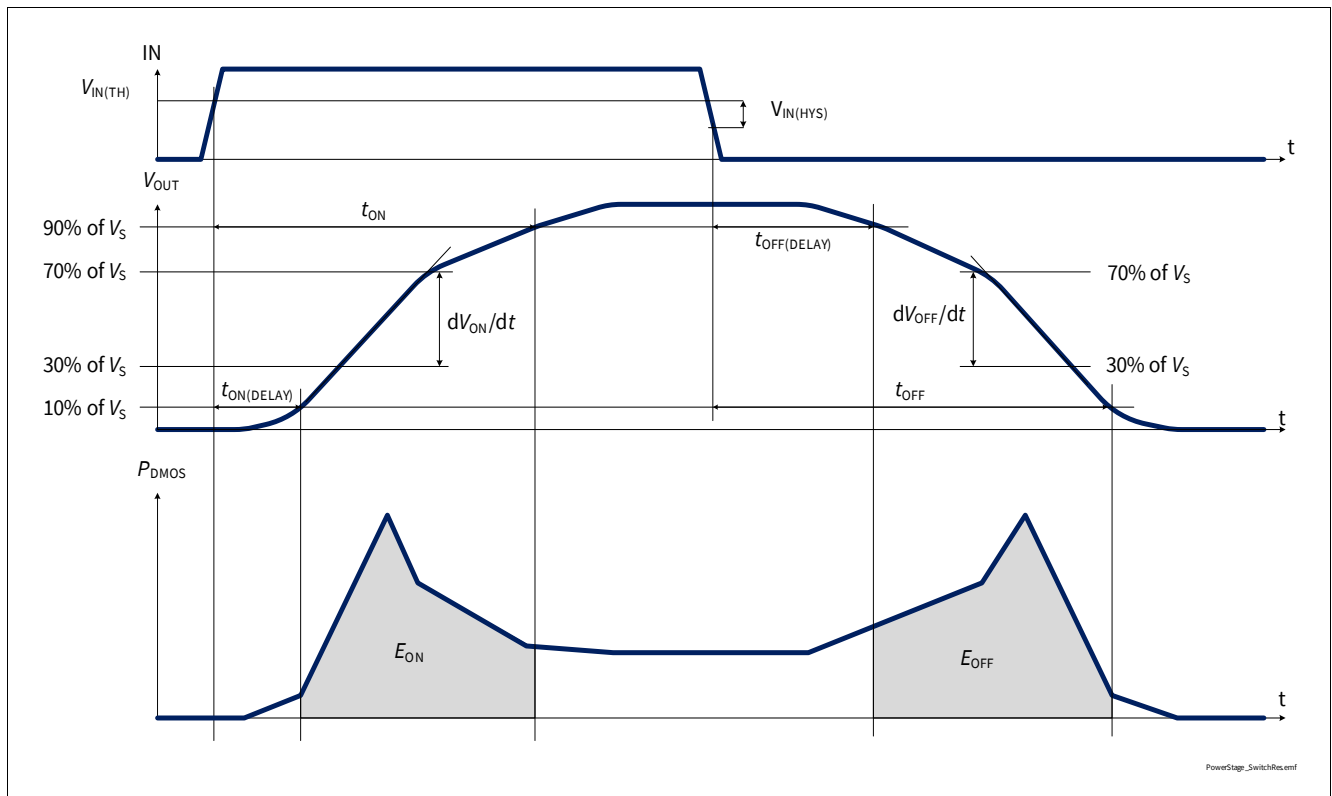


Figure 16 Switching a Resistive Load

7.2.2 Switching Inductive Loads

When switching OFF inductive loads with high-side switches, the voltage V_{OUT} drops below ground potential, because the inductance intends to continue driving the current. To prevent the destruction of the device due to overvoltage, a voltage clamp mechanism is implemented. The clamping structure limits the negative output voltage so that $V_{DS} = V_{DS(CLAMP)}$. **Figure 17** shows a concept drawing of the implementation. The clamping structure protects the device in all operation modes listed in [Chapter 6.1](#).

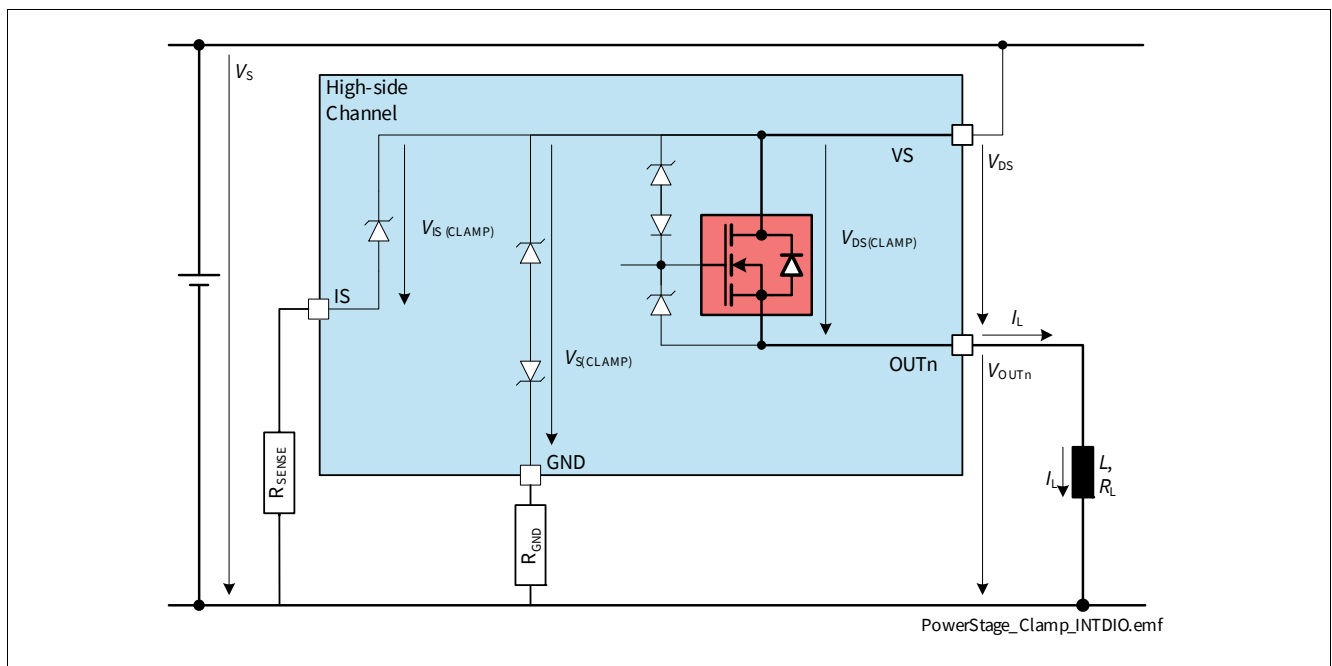


Figure 17 Output Clamp concept

Power Stages

During demagnetization of inductive loads, energy has to be dissipated in BTS7008-2EPA. The energy can be calculated with [Equation \(7.1\)](#):

$$E = V_{DS(CLAMP)} \cdot \left[\frac{V_S - V_{DS(CLAMP)}}{R_L} \cdot \ln \left(1 - \frac{R_L \cdot I_L}{V_S - V_{DS(CLAMP)}} \right) + I_L \right] \cdot \frac{L}{R_L} \quad (7.1)$$

The maximum energy, therefore the maximum inductance for a given current, is limited by the thermal design of the component. Please refer to [Chapter 4.2](#) for the maximum allowed values of E_{AS} (single pulse energy) and E_{AR} (repetitive energy).

7.2.3 Output Voltage Limitation

To increase the current sense accuracy, V_{DS} voltage is monitored. When the output current I_L decreases while the channel is diagnosed (DEN pin set to “high”, channel selected with DSEL pins - see [Figure 18](#)) bringing V_{DS} equal or lower than $V_{DS(SLC)}$, the output DMOS gate is partially discharged. This increases the output resistance so that $V_{DS} = V_{DS(SLC)}$ even for very small output currents. The V_{DS} increase allows the current sensing circuitry to work more efficiently, providing better k_{ILIS} accuracy for output current in the low range.

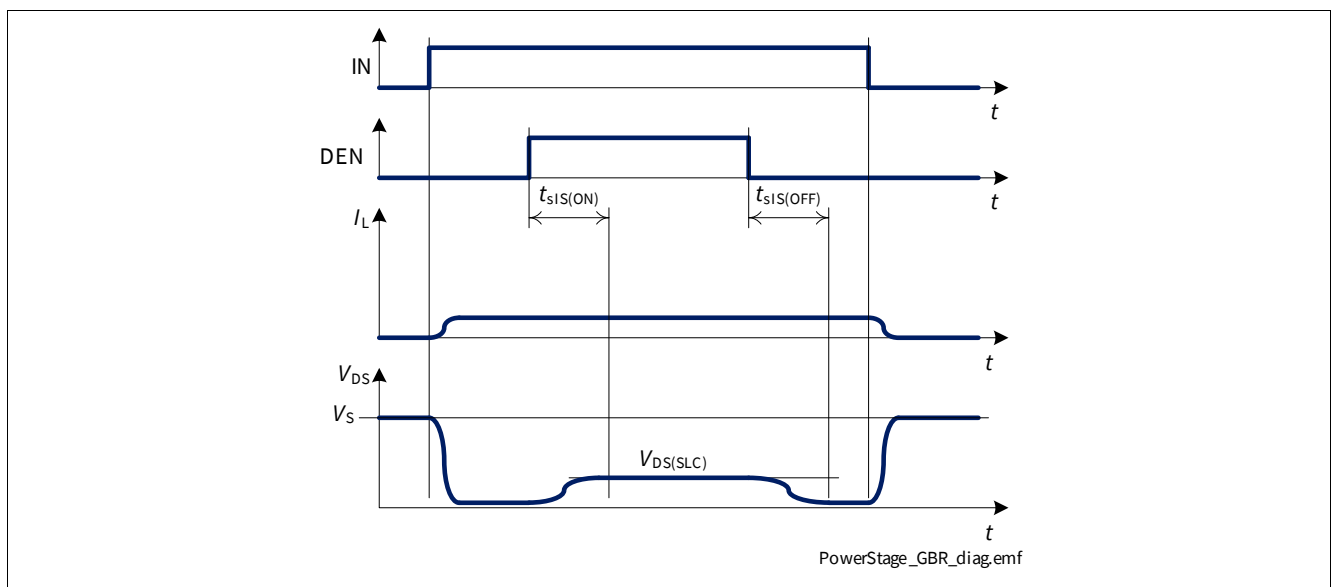


Figure 18 Output Voltage Limitation activation during diagnosis

7.3 Advanced Switching Characteristics

7.3.1 Inverse Current behavior

When $V_{OUT} > V_S$, a current I_{INV} flows into the power output transistor (see [Figure 19](#)). This condition is known as “Inverse Current”.

If the channel is in OFF- state, the current flows through the intrinsic body diode generating high power losses therefore an increase of overall device temperature. This may lead to a switch OFF of unaffected channels due to Over Temperature. If the channel is in ON- state, $R_{DS(INV)}$ can be expected and power dissipation in the output stage is comparable to normal operation in $R_{DS(ON)}$.

During Inverse Current condition, the channel remains in ON- or OFF- state as long as $I_{INV} < I_{L(INV)}$. If one channel has inverse current applied, the neighbor channel is not influenced, meaning that switching ON and OFF

Power Stages

timings, protection (Over Current, Over Temperature) and current sensing (k_{ILIS}) are still within specified limits.

With InverseON, it is possible to switch ON the channel during Inverse Current condition as long as $I_{INV} < I_{L(INV)}$ (see Figure 20).

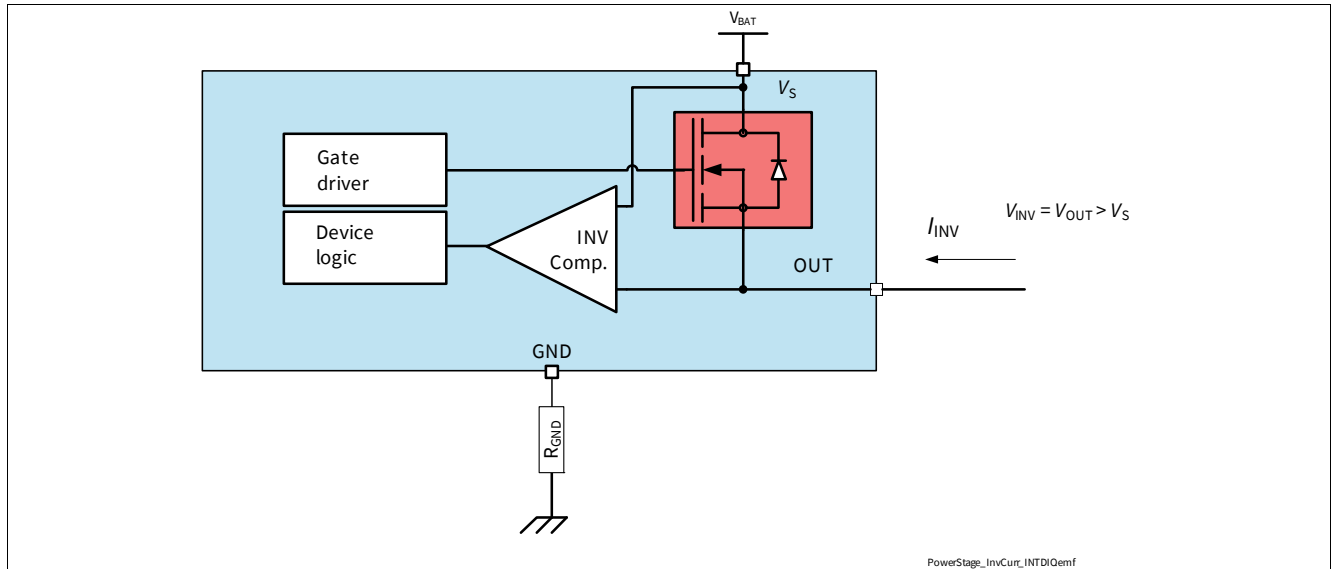


Figure 19 Inverse Current Circuitry

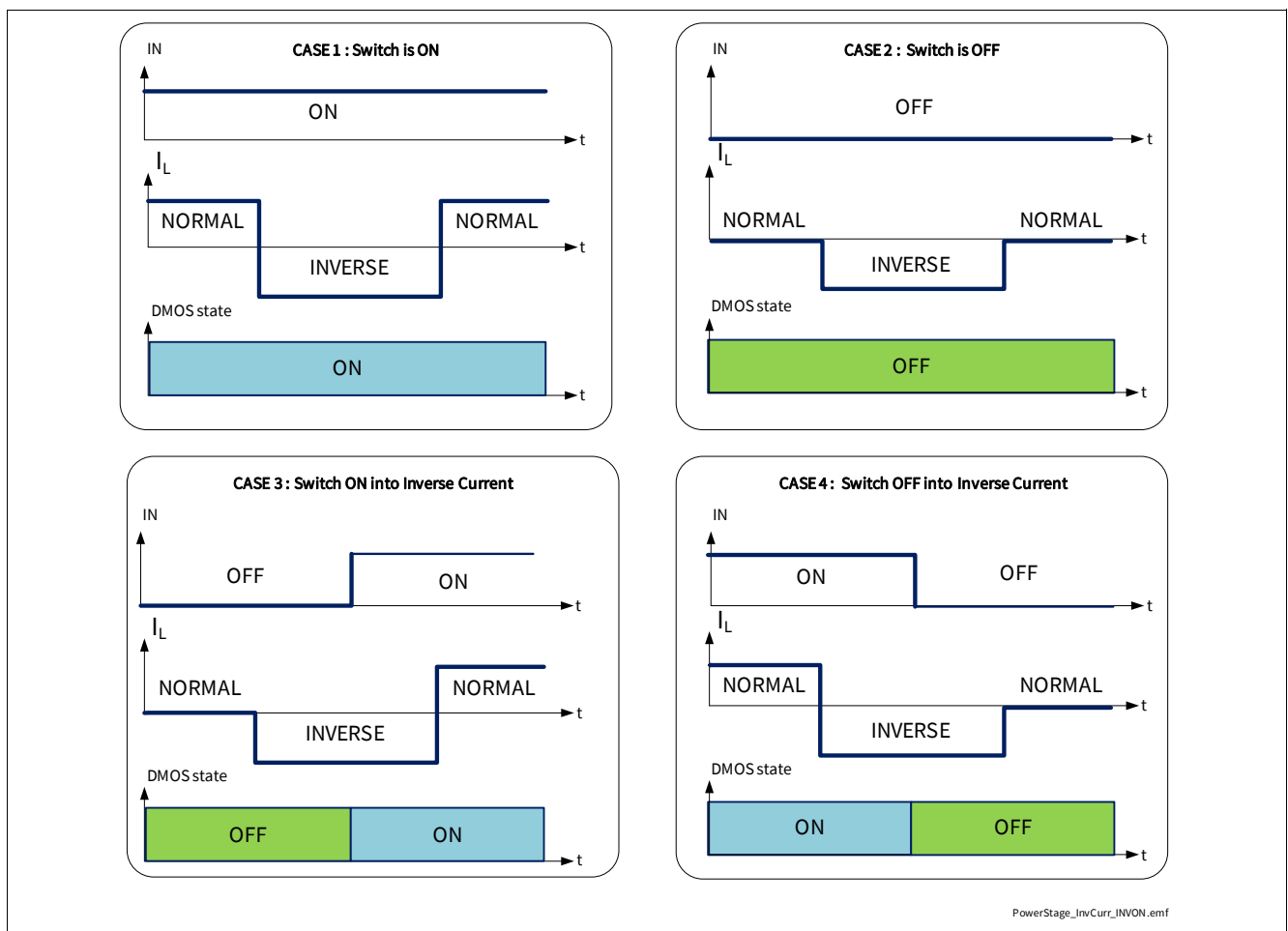


Figure 20 InverseON - Channel behavior in case of applied Inverse Current

Power Stages

Note: No protection mechanism like Over Temperature or Overload protection is active during applied Inverse Currents.

7.3.2 Switching Channels in Parallel

In case of appearance of a short circuit with connected in parallel to drive a single load, it may happen that the two channels switch OFF asynchronously, therefore bringing an additional thermal stress to the channel that switches OFF last. For this reason it is not recommended to use the device with channels in parallel.

7.3.3 Cross Current robustness with H-Bridge configuration

When BTS7008-2EPA is used as high-side switch e.g. in a bridge configuration (therefore paired with a low-side switch as shown in Figure 21), the maximum slew rate applied to the output by the low-side switch must be lower than $|dV_{OUT} / dt|$. Otherwise the output stage may turn ON in linear mode (not in $R_{DS(ON)}$) while the low-side switch is commutating. This creates an unprotected over heating situation for the DMOS due to the cross-conduction current.

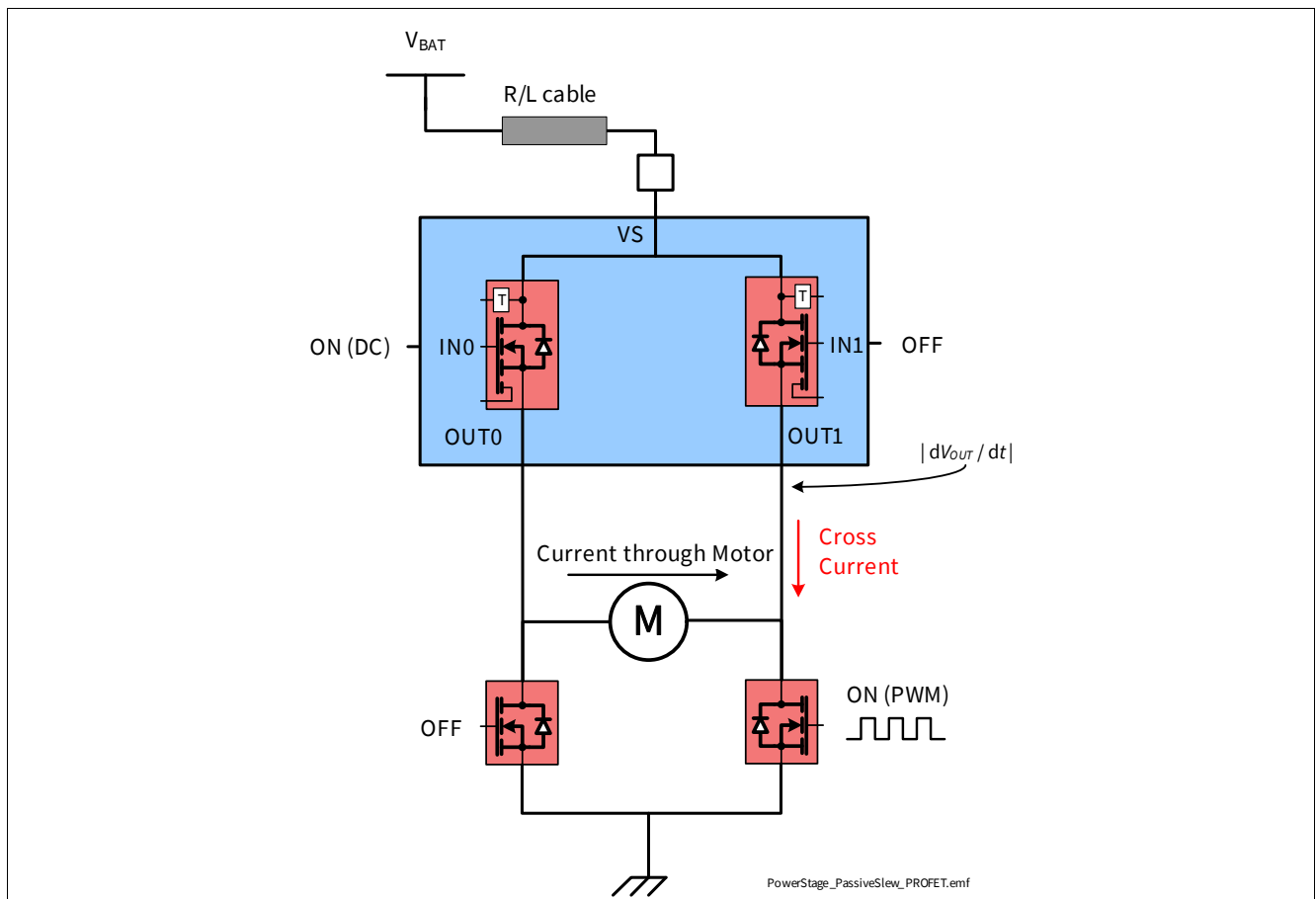


Figure 21 High Side switch used in Bridge configuration